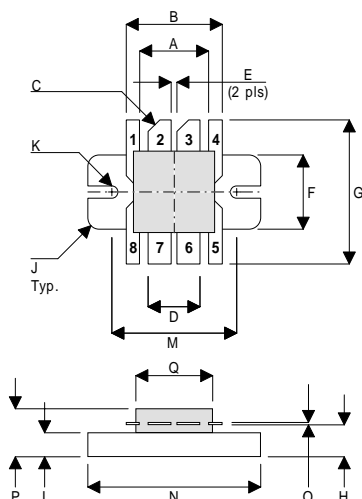


MECHANICAL DATA



DD

PIN 1	SOURCE (COMMON)	PIN 2	DRAIN 1
PIN 3	DRAIN 2	PIN 4	SOURCE (COMMON)
PIN 5	SOURCE (COMMON)	PIN 6	GATE 2
PIN 7	GATE 1	PIN 8	SOURCE (COMMON)

DIM	mm	Tol.	Inches	Tol.
A	9.14	0.13	0.360	0.005
B	12.70	0.13	0.500	0.005
C	45°	5°	45°	5°
D	6.86	0.13	0.270	0.005
E	0.76	0.13	0.030	0.005
F	9.78	0.13	0.385	0.005
G	19.05	0.25	0.750	0.010
H	4.19	0.13	0.165	0.005
I	3.17	0.13	0.125	0.005
J	1.52R	0.13	0.060R	0.005
K	1.65R	0.13	0.065R	0.005
M	16.51	0.13	0.650	0.005
N	22.86	0.13	0.900	0.005
O	0.13	0.02	0.005	0.001
P	6.35	0.64	0.250	0.025
Q	10.77	0.13	0.424	0.005

**GOLD METALLISED  
MULTI-PURPOSE SILICON  
DMOS RF FET  
80W – 28V – 400MHz  
PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW  $C_{rss}$
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 13 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS  
from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS ( $T_{case} = 25^{\circ}C$  unless otherwise stated)

$P_D$	Power Dissipation	175W
$BV_{DSS}$	Drain – Source Breakdown Voltage *	70V
$BV_{GSS}$	Gate – Source Breakdown Voltage *	±20V
$I_{D(sat)}$	Drain Current *	10A
$T_{stg}$	Storage Temperature	-65 to 150°C
$T_j$	Maximum Operating Junction Temperature	200°C

\* Per Side

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## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>PER SIDE</b>					
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage V <sub>GS</sub> = 0 I <sub>D</sub> = 100mA	70			V
I <sub>D</sub> DSS	Zero Gate Voltage Drain Current V <sub>DS</sub> = 28V V <sub>GS</sub> = 0			2	mA
I <sub>G</sub> DSS	Gate Leakage Current V <sub>GS</sub> = 20V V <sub>DS</sub> = 0			1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage * I <sub>D</sub> = 10mA V <sub>DS</sub> = V <sub>GS</sub>	1		7	V
g <sub>fs</sub>	Forward Transconductance * V <sub>DS</sub> = 10V I <sub>D</sub> = 2A	1.6			S
<b>TOTAL DEVICE</b>					
G <sub>PS</sub>	Common Source Power Gain P <sub>O</sub> = 80W	13			dB
η	Drain Efficiency V <sub>DS</sub> = 28V I <sub>DQ</sub> = 0.8A	50			%
VSWR	Load Mismatch Tolerance f = 500MHz	20:1			—
<b>PER SIDE</b>					
C <sub>iss</sub>	Input Capacitance V <sub>DS</sub> = 28V V <sub>GS</sub> = -5V f = 1MHz			120	pF
C <sub>oss</sub>	Output Capacitance V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			60	pF
C <sub>rss</sub>	Reverse Transfer Capacitance V <sub>DS</sub> = 28V V <sub>GS</sub> = 0 f = 1MHz			5	pF

\* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

## HAZARDOUS MATERIAL WARNING

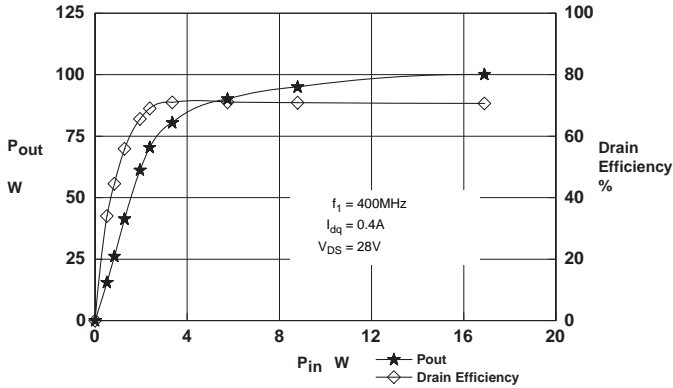
The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

**THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.**

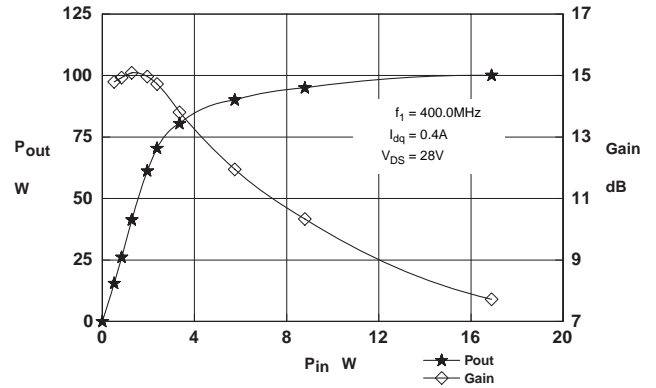
## THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 1°C / W
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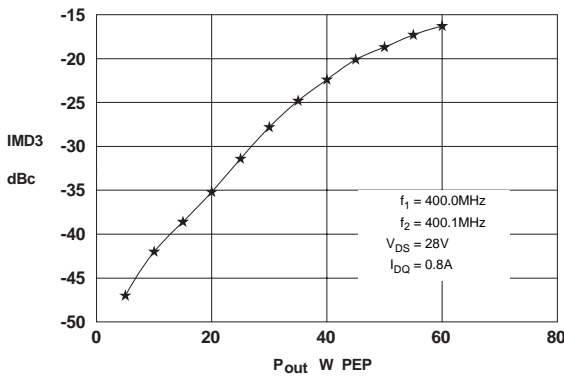
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**Figure 1 – Power Output and Efficiency vs. Power Input.**



**Figure 2 – Power Output & Gain vs. Power Input.**



**Figure 3 – IMD vs. Output Power.**

## D1034UK OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z <sub>S</sub> Ω	Z <sub>L</sub> Ω
400	1.5 + j0.2	5.0 + j2.0

### Typical S Parameters

! Vds=28V, Idq=1A  
# MHz S MA R 50

!Freq MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
100	0.794	-158	14.622	69	0.0115	-7	0.61	-145
200	0.881	-167	5.821	42	0.0061	3	0.794	-156
300	0.923	-171	3.02	28	0.0068	60	0.871	-162
400	0.923	-176	1.82	18	0.117	77	0.902	-167
500	0.937	-179	1.439	15	0.0168	76	0.923	-169
600	0.952	177	1.057	13	0.0234	75	0.945	-171
700	0.966	174	0.676	10	0.0285	74	0.966	-174
800	0.966	171	0.543	5	0.0335	69	0.955	-177
900	0.977	167	0.447	1	0.0394	64	0.966	178
1000	0.966	165	0.359	1	0.0432	64	0.955	178

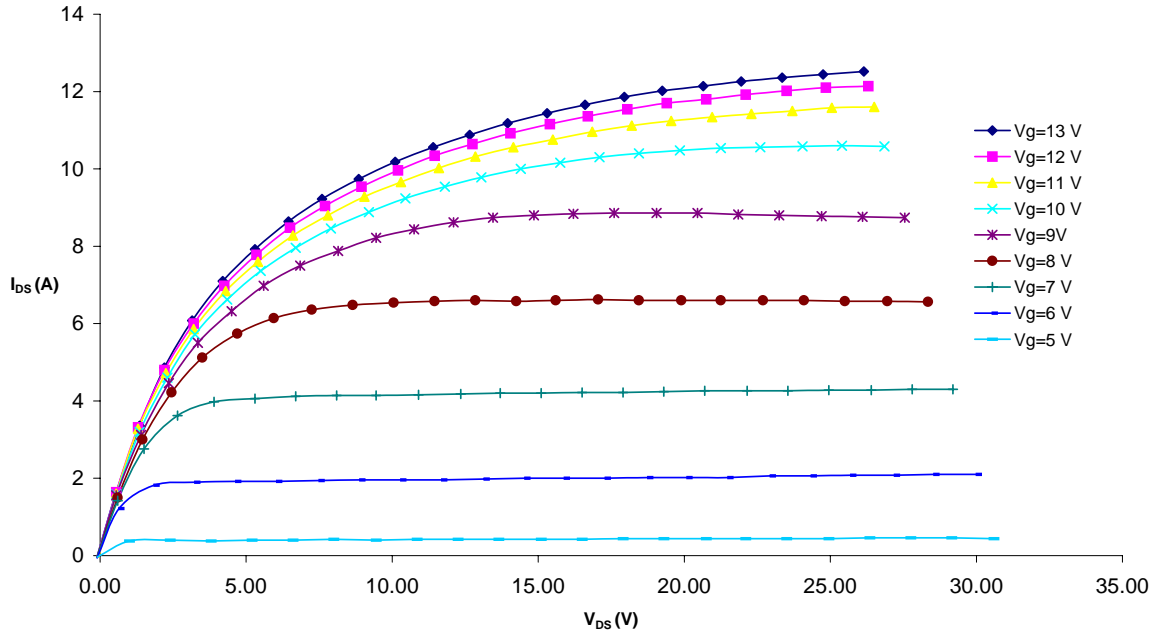


Figure 4 – Typical IV Characteristics.

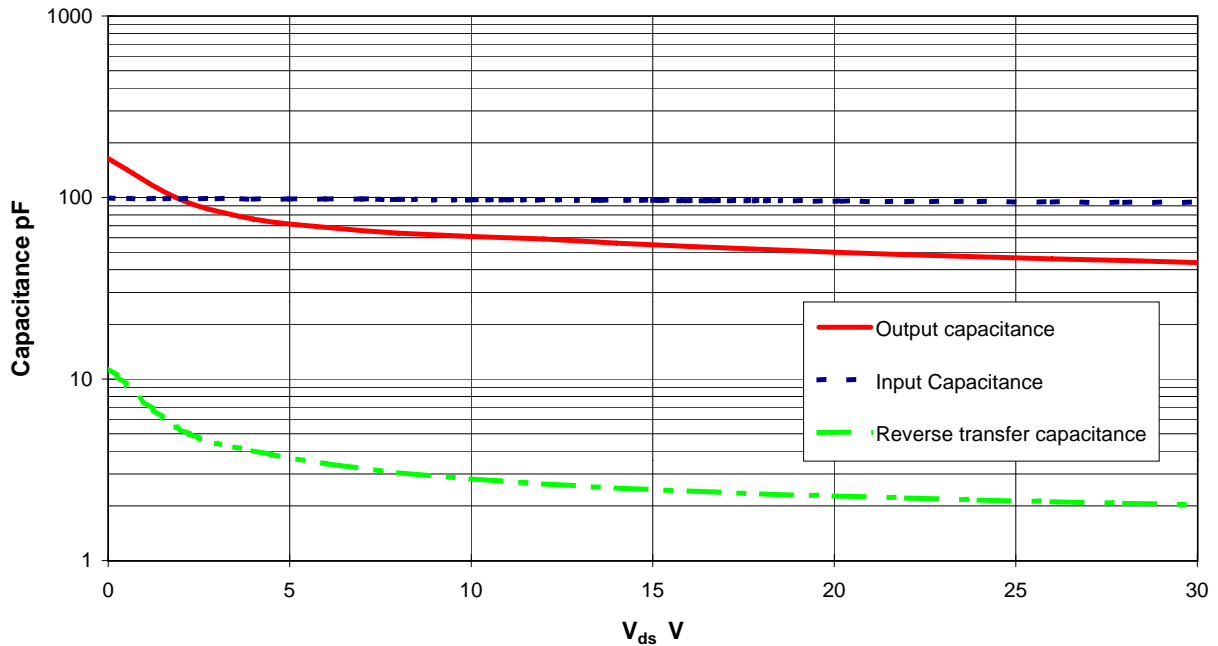
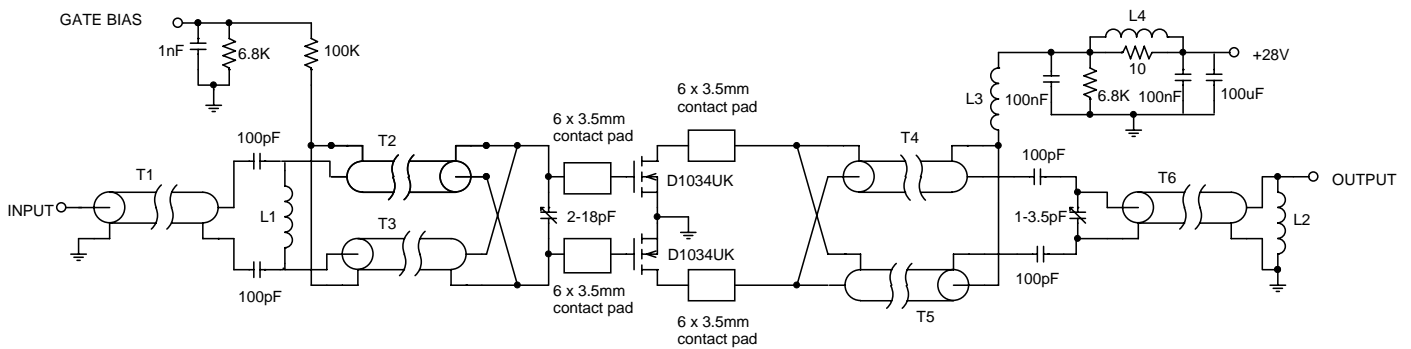


Figure 5 – Typical CV Characteristics.

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## D1034UK TEST FIXTURE

Substrate 1.6mm PTFE/glass, Er=2.5  
All microstrip lines W=4.4mm

T1	70mm	50Ω	UT34	SEMI RIGID COAX	L1	3.5 turns of 24swg ECW, 3mm ID
T2,T3	85mm	25Ω	UT70-25	SEMI RIGID COAX	L2	5.5 turns of 24swg ECW, 4mm ID
T4,T5	100mm	15Ω	UT85-15	SEMI RIGID COAX	L3	4 turns of 21swg ECW, 7mm ID
T6	70mm	50Ω	UT85	SEMI RIGID COAX	L4	3 turns of 21swg ECW on Fair-Rite FT50-75 core

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